

U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.352US0		10/799,060	
				Applicant(s)			
(Use several sheets if necessary)				Jeffrey Lutze et al.			
				Filing Date		Group	
				March 12, 2004		2818	
U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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Examiner	Date Considered			08/11/05			
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Examiner <i>M. S. Kurihara</i>			Date Considered <i>8/11/05</i>				
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Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
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